

I. BOOKS, CHAPTERS, and REVIEWS

N.T. Bagraev, V.V. Emtsev, and S.K. Estreicher (editors), *Proceedings of the 25<sup>th</sup> International Conference on Defects in Semiconductors*, **Physica B** vol (Elsevier, Amsterdam, 2009), p.

S.K. Estreicher, D. Backlund, T.M. Gibbons, and A. Doçaj: *Vibrational properties of impurities in semiconductors*, **Model. Simul. Mater. Sci. Engr.** vol, pages (2009)

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S.K. Estreicher, M.W. Holtz, C.H. Seager, and A.F. Wright (editors), *Proceedings of the 24<sup>th</sup> International Conference on Defects in Semiconductors*, **Physica B** 401-402 (Elsevier, Amsterdam, 2007)

D.A. Drabold and S.K. Estreicher (editors), *Theory of Defects in Semiconductors*, vol. 104 in **Topics in Applied Physics** (Springer, Heidelberg, 2007), ISBN: 3-540-33400-9

D.A. Drabold and S.K. Estreicher: *Defect Theory: an Armchair History*, in **Theory of Defects in Semiconductors**, ed. D.A. Drabold and S.K. Estreicher (Springer, Berlin, 2007), p. 11-27

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S.K. Estreicher: *Structure and Dynamics of Point Defects in Crystalline Silicon*, in **Atomistic Modeling of Materials Properties and Phenomena**, ed. T. Frauenheim, M. Pederson, and P. Deak (Wiley-VCH, Berlin), **Physica Status Solidi (b)** 217, 513-532 (2000)

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## 2. RESEARCH and INVITED PAPERS

T.M. Gibbons and S.K. Estreicher: *Impact of impurities on the thermal conductivity of semiconductor nanostructures: first-principles theory* **Physical Review Letters** **102**, 255502/1-4 (2009) and **103**, 099904/1-2 (2009) (Erratum)  
This paper has been selected by the Editors for publication in the July 6, 2009 issue of **Virtual Journal of Nanoscale Science & Technology** (AIP/APS)

S.K. Estreicher and T.M. Gibbons: *Non-equilibrium molecular-dynamics for impurities in semiconductors: vibrational lifetimes and thermal conductivities* **(invited)** **Physica B** (2009)

S.K. Estreicher, D. Backlund, and T.M. Gibbons: *Theory of Defects in Si and Ge: past, present and recent developments* **(invited)** **Thin Solid Films** (2009)

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- A. Carvalho, R. Jones, M. Sanati, S.K. Estreicher, J. Coutinho, and P.R. Briddon: *First-principles investigation of a metastable boron-oxygen interstitial pair in Si*  
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### **3. CONTRIBUTED CONFERENCE PAPERS and MISCELLANEOUS PUBLICATIONS**

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